

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	5	V
Peak Pulse Collector Current	I _{CM}	3	A
Continuous Collector Current	I _C	2	A
Peak Base Current	I _{BM}	0.3	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	730	mW
Power Dissipation (Note 7)	P _D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	R _{θJA}	171	°C/W
Thermal Resistance, Junction to Ambient Air (Note 7)	R _{θJA}	209	°C/W
Thermal Resistance, Junction to Lead (Note 8)	R _{θJL}	75	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

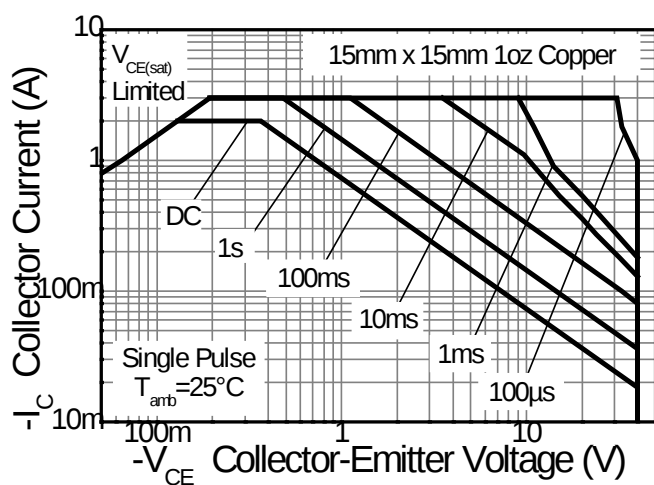
ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	C

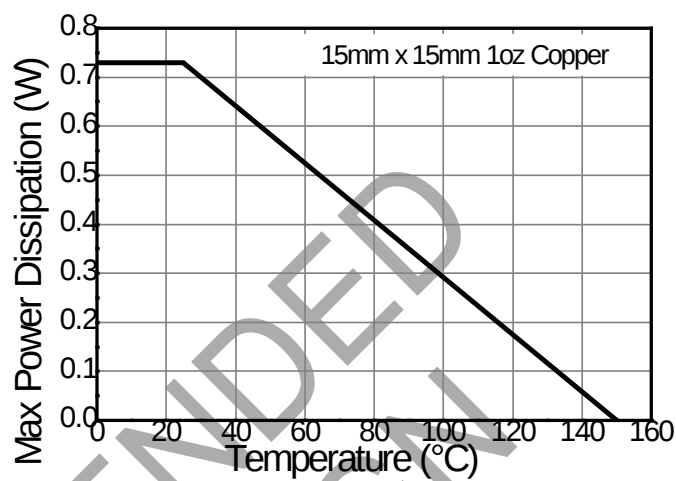
Notes:

6. For a device mounted with the collector lead on 15mm × 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
7. Same as Note 5, except the device is mounted on minimum recommended pad layout.
8. Thermal resistance from junction to solder point (at the end of the collector lead).
9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

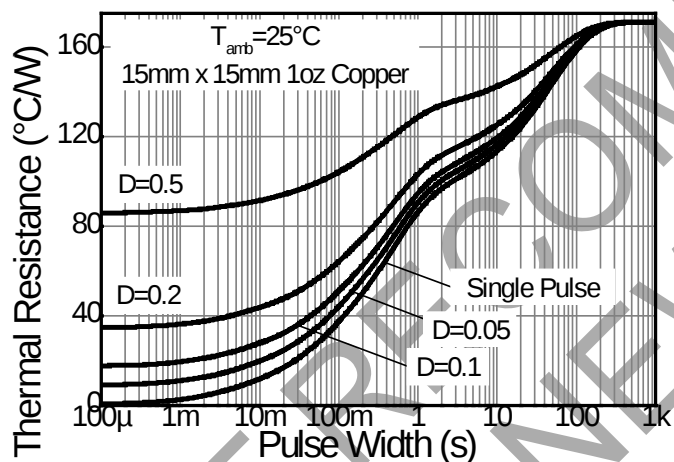
Thermal Characteristics and Derating Information



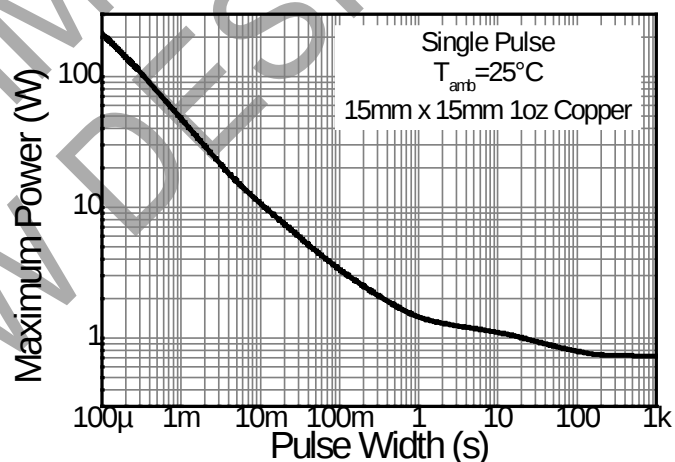
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	40	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	40	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	5	—	—	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}	—	—	100	nA	V _{CB} = 30V, I _E = 0
Emitter-Base Cutoff Current	I _{EBO}	—	—	50	μA	V _{CB} = 30V, I _E = 0, T _A = +150°C
		—	—	100	nA	V _{EB} = 4V, I _C = 0
ON CHARACTERISTICS (Note 8)						
DC Current Gain	h _{FE}	350	—	—		V _{CE} = 2V, I _C = 0.1A
		300	—	—		V _{CE} = 2V, I _C = 0.5A
		300	—	—		V _{CE} = 2V, I _C = 1A
		150	—	—		V _{CE} = 2V, I _C = 2A
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	—	70	mV	I _C = 100mA, I _B = 1mA
		—	30	100		I _C = 500mA, I _B = 50mA
		—	—	180		I _C = 750mA, I _B = 15mA
		—	—	180		I _C = 1A, I _B = 50mA
		—	—	320		I _C = 2A, I _B = 200mA
Equivalent On-Resistance	R _{CE(sat)}	—	60	200	mΩ	I _C = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	—	—	1.1	V	I _C = 2A, I _B = 200mA
Base-Emitter Turn-on Voltage	V _{BE(on)}	—	—	0.75	V	V _{CE} = 2V, I _C = 100mA
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	100	—	—	MHz	V _{CE} = 10V, I _C = 100mA, f = 100MHz
Output Capacitance	C _{ob}	—	—	20	pF	V _{CB} = 10V, f = 1MHz

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

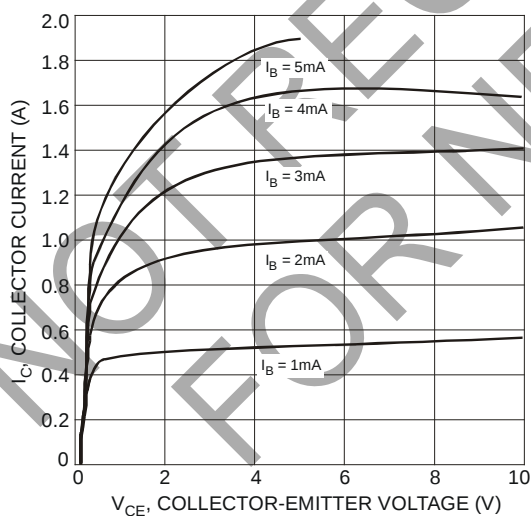


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

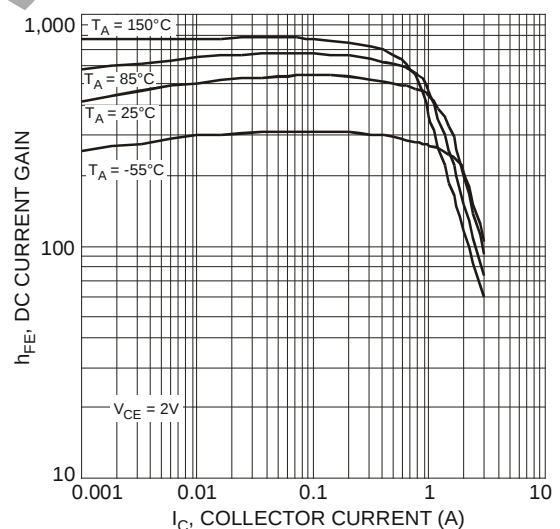


Fig. 3 Typical DC Current Gain vs. Collector Current

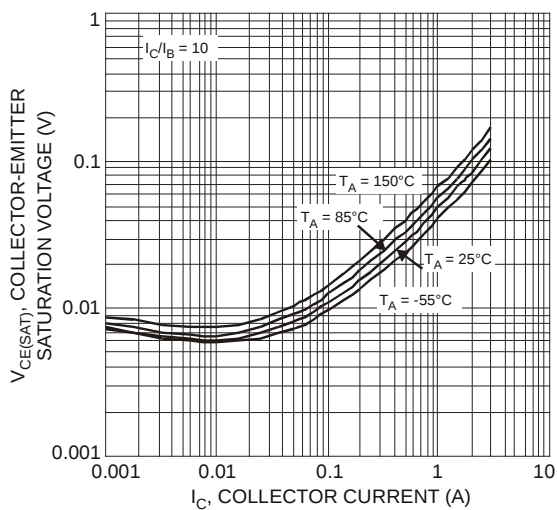


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

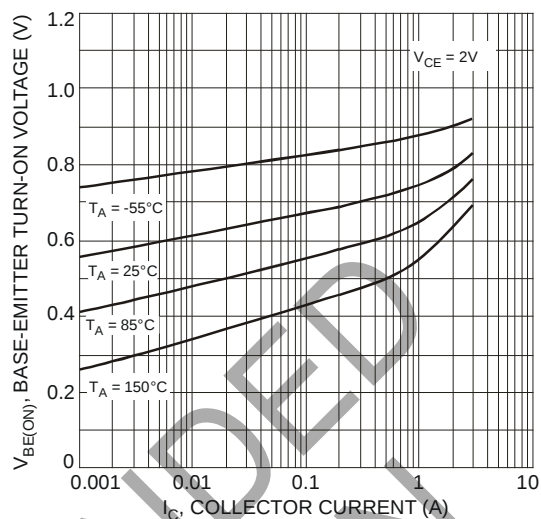


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

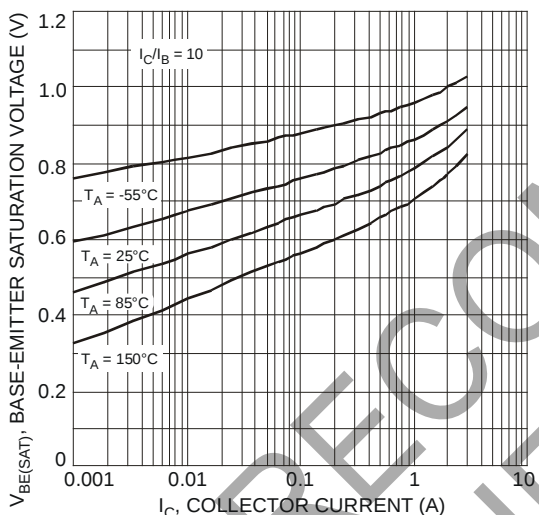


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

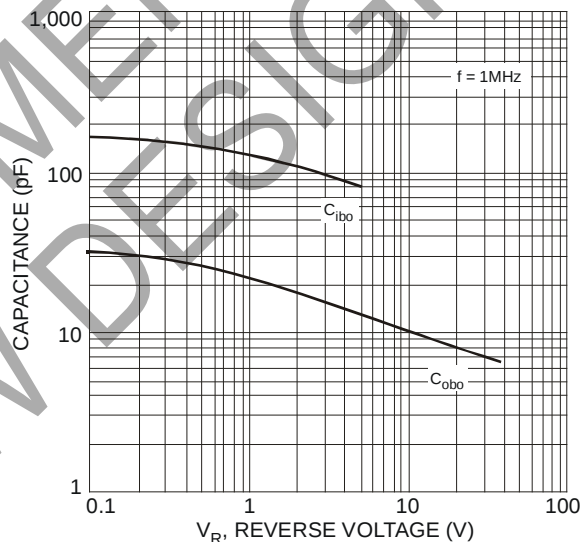


Fig. 7 Typical Capacitance Characteristics

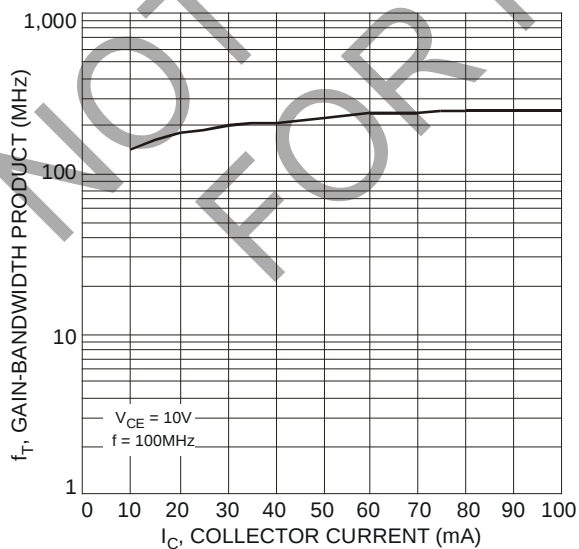
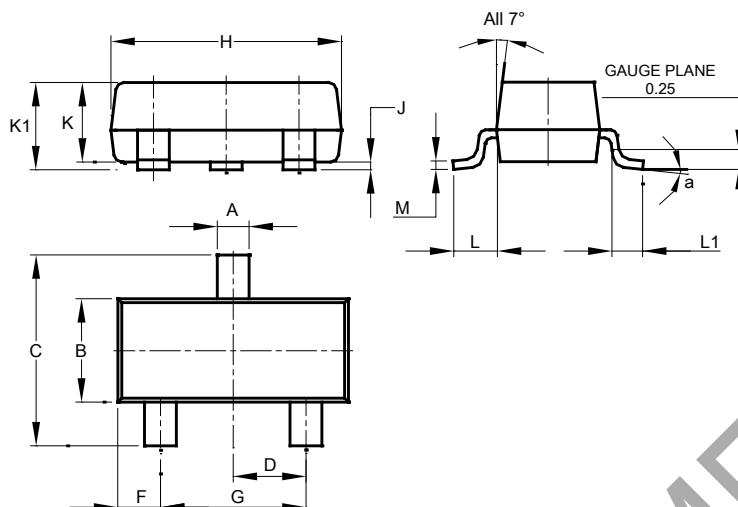


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

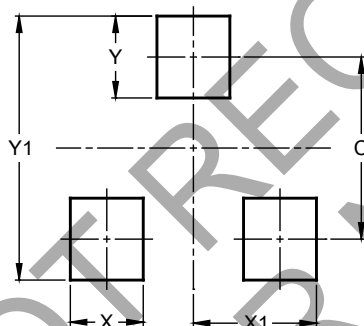


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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